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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I ² C, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	14
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	768 x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 11x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	20-LSSOP (0.173", 4.40mm Width)
Supplier Device Package	20-LSSOP
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f10268gsp-x5

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

O ROM, RAM capacities

Code flash	Data flash	RAM	20 pins	24 pins	30 pins
16 KB	2 KB	2 KB	_	_	R5F102AA
	_		_	_	R5F103AA
	2 KB	1.5 KB	R5F1026A Note 1	R5F1027A Note 1	_
	_		R5F1036A Note 1	R5F1037A Note 1	_
12 KB	2KB	1 KB	R5F10269 Note 1	R5F10279 Note 1	R5F102A9
	_		R5F10369 Note 1	R5F10379 Note 1	R5F103A9
8 KB	2 KB	768 B	R5F10268 Note 1	R5F10278 Note 1	R5F102A8
	_		R5F10368 Note 1	R5F10378 Note 1	R5F103A8
4 KB	2KB	512 B	R5F10267	R5F10277	R5F102A7
	_		R5F10367	R5F10377	R5F103A7
2 KB	2 KB	256 B	R5F10266 Note 2	_	_
	_		R5F10366 Note 2	_	_

Notes 1. This is 640 bytes when the self-programming function or data flash function is used. (For details, see CHAPTER 3 CPU ARCHITECTURE.)

2. The self-programming function cannot be used for R5F10266 and R5F10366.

Caution When the flash memory is rewritten via a user program, the code flash area and RAM area are used because each library is used. When using the library, refer to RL78 Family Flash Self Programming Library Type01 User's Manual and RL78 Family Data Flash Library Type04 User's Manual.

1.3.2 On-chip oscillator characteristics

(1) High-speed on-chip oscillator oscillation frequency of the R5F102 products

Oscillator	Condition	MIN	MAX	Unit
High-speed on-chip	T _A = -20 to +85 °C	-1.0	+1.0	%
oscillator oscillation	T _A = -40 to -20 °C	-1.5	+1.5	
frequency accuracy	T _A = +85 to +105 °C	-2.0	+2.0	

(2) High-speed on-chip oscillator oscillation frequency of the R5F103 products

Oscillator	Condition	MIN	MAX	Unit
High-speed on-chip	$T_A = -40 \text{ to} + 85 ^{\circ}\text{C}$	-5.0	+5.0	%
oscillator oscillation				
frequency accuracy				

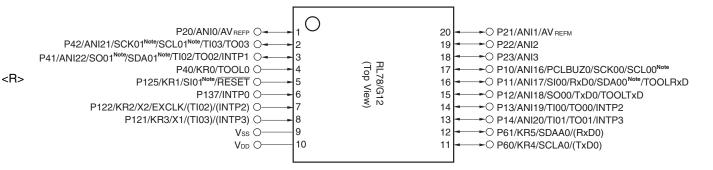
1.3.3 Peripheral Functions

The following are differences in peripheral functions between the R5F102 products and the R5F103 products.

		R5F102	2 product	R5F103 product		
RL78/G12	20, 24 pin	30 pin product	20, 24 pin	30 pin		
	product		product	product		
Serial interface	UART	1 channel	3 channels	1 channel		
	CSI	2 channels	3 channels	1 channel		
	Simplified I ² C	2 channels	3 channels	None		
DMA function		2 channels		None		
Safety function	CRC operation	Yes		None		
	RAM guard	Yes		None		
	SFR guard	Yes		None		

- 1.4 Pin Configuration (Top View)
- 1.4.1 20-pin products

• 20-pin plastic LSSOP (4.4×6.5 mm, 0.65 mm pitch)



Note Provided only in the R5F102 products.

- Remarks 1. For pin identification, see 1.5 Pin Identification.
 - 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). See Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR).

1.5 Pin Identification

ANI0 to ANI3,		REGC:	Regulator Capacitance
ANI16 to ANI22:	Analog input	RESET:	Reset
AVREFM:	Analog Reference Voltage Minus	RxD0 to RxD2:	Receive Data
AVREFP:	Analog reference voltage plus	SCK00, SCK01, SCK11,	
EXCLK:	External Clock Input	SCK20:	Serial Clock Input/Output
	(Main System Clock)	SCL00, SCL01,	
INTP0 to INTP5	Interrupt Request From Peripheral	SCL11, SCL20, SCLA0:	Serial Clock Input/Output
KR0 to KR9:	Key Return	SDA00, SDA01, SDA11,	
P00 to P03:	Port 0	SDA20, SDAA0:	Serial Data Input/Output
P10 to P17:	Port 1	SI00, SI01, SI11, SI20:	Serial Data Input
P20 to P23:	Port 2	SO00, SO01, SO11,	
P30 to P31:	Port 3	SO20:	Serial Data Output
P40 to P42:	Port 4	TI00 to TI07:	Timer Input
P50, P51:	Port 5	TO00 to TO07:	Timer Output
P60, P61:	Port 6	TOOL0:	Data Input/Output for Tool
P120 to P122, P125:	Port 12	TOOLRxD, TOOLTxD:	Data Input/Output for External
P137:	Port 13		Device
P147:	Port 14	TxD0 to TxD2:	Transmit Data
PCLBUZ0, PCLBUZ1:	Programmable Clock Output/	VDD:	Power supply
	Buzzer Output	Vss:	Ground
		X1, X2:	Crystal Oscillator (Main System Clock)

2.2 Oscillator Characteristics

2.2.1 X1 oscillator characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation	Ceramic resonator /	$2.7~V \leq V_{DD} \leq 5.5~V$	1.0		20.0	MHz
frequency (fx) ^{Note}	crystal oscillator	1.8 V ≤ V _{DD} < 2.7 V	1.0		8.0	

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator, refer to 5.4 System Clock Oscillator.

2.2.2 On-chip oscillator characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Oscillators	Parameters	Conditions		MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	fін					24	MHz
High-speed on-chip oscillator		R5F102 products	$T_A = -20 \text{ to } +85^{\circ}\text{C}$	-1.0		+1.0	%
clock frequency accuracy			$T_A = -40 \text{ to } -20^{\circ}\text{C}$	-1.5		+1.5	%
		R5F103 products		-5.0		+5.0	%
Low-speed on-chip oscillator clock frequency	fıL				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H) and bits 0 to 2 of HOCODIV register.

2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.

 $(TA = -40 \text{ to } +85^{\circ}C, 1.8 \text{ V} \le VDD \le 5.5 \text{ V}, Vss = 0 \text{ V})$

(4/4)

Parameter	Symbol		Condition	ons	MIN.	TYP.	MAX.	Unit
Output voltage, low	V _{OL1}	20-, 24-pin product P00 to P03 ^{Note} , P10 P40 to P42		$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OL1} = 20.0 \text{ mA}$ $4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$			1.3 0.7	V
		P10 to P17, P30, F	30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147				0.6	V
				$2.7~V \leq V_{DD} \leq 5.5~V,$ $I_{OL1} = 1.5~mA$			0.4	V
				$1.8~V \leq V_{DD} \leq 5.5~V,$ $I_{OL1} = 0.6~mA$			0.4	V
	V _{OL2}	P20 to P23		Iol2 = 400 μA			0.4	V
	V _{OL3}	P60, P61		$4.0~V \leq V_{DD} \leq 5.5~V,$ $I_{OL1} = 15.0~mA$			2.0	V
				$4.0~V \leq V_{DD} \leq 5.5~V,$ $I_{OL1} = 5.0~mA$			0.4	V
				$2.7~V \leq V_{DD} \leq 5.5~V,$ $I_{OL1} = 3.0~mA$			0.4	V
				$1.8~V \leq V_{DD} \leq 5.5~V,$ $I_{OL1} = 2.0~mA$			0.4	V
Input leakage current, high	Ішн1	Other than P121, $V_1 = V_{DD}$ P122					1	μΑ
	І Lін2	P121, P122 (X1, X2/EXCLK)	$V_{I} = V_{DD}$	Input port or external clock input			1	μΑ
				When resonator connected			10	μΑ
Input leakage current, low	ILIL1	Other than P121, P122	Vı = Vss				-1	μΑ
	ILIL2	P121, P122 (X1, X2/EXCLK)	Vı = Vss	Input port or external clock input			-1	μΑ
				When resonator connected			-10	μΑ
On-chip pull-up resistance	Rυ	20-, 24-pin products: P00 to P03 ^{Note} , P10 to P14, P40 to P42, P125, RESET 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147		V _I = Vss, input port	10	20	100	kΩ

Note 24-pin products only.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

2.3.2 Supply current characteristics

(1) 20-, 24-pin products

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

(1/2)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit		
Supply	I _{DD1}	Operating	HS(High-speed	f⊩ = 24 MHz ^{Note 3}	Basic	V _{DD} = 5.0 V		1.5		mA		
current ^{Note 1}		mode	main) mode Note 4		operation	V _{DD} = 3.0 V		1.5				
					Normal	V _{DD} = 5.0 V		3.3	5.0	mA		
					operation	V _{DD} = 3.0 V		3.3	5.0			
				f⊩ = 16 MHz ^{Note 3}		V _{DD} = 5.0 V		2.5	3.7	mA		
						V _{DD} = 3.0 V		2.5	3.7			
			LS(Low-speed	f⊩ = 8 MHz ^{Note 3}		V _{DD} = 3.0 V		1.2	1.8	mA		
		main) mode ^{Note 4}			V _{DD} = 2.0 V		1.2	1.8				
	$ \begin{array}{c c} \text{HS(High-speed} & \text{f}_{\text{MX}} = 20 \text{ MHz}^{\text{Note 2}}, \\ \text{main)} & \text{mode}^{\text{Note 4}} & \text{V}_{\text{DD}} = 5.0 \text{ V} \end{array} $		Square wave input		2.8	4.4	mA					
			main) mode Note $V_{DD} = 5.0 \text{ V}$ $f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	$V_{DD} = 5.0 \text{ V}$		Resonator connection		3.0	4.6			
					Square wave input		2.8	4.4	mA			
				$V_{DD} = 3.0 \text{ V}$		Resonator connection		3.0	4.6			
				ı		$f_{MX} = 10 \text{ MHz}^{Note 2},$		Square wave input		1.8	2.6	mA
				$V_{DD} = 5.0 \text{ V}$		Resonator connection		1.8	2.6			
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$		Square wave input		1.8	2.6	mA		
				$V_{DD} = 3.0 \text{ V}$		Resonator connection		1.8	2.6			
	· · · · · · · · · · · · · · · · · · ·	LS(Low-speed	$f_{MX} = 8 \text{ MHz}^{Note 2},$	$f_{MX} = 8 \text{ MHz}^{\text{Note 2}},$	Square wave input		1.1	1.7	mA			
		main) mode Note 4	main) mode Note 4 $V_{DD} = 3.0 \text{ V}$		Resonator connection		1.1	1.7				
				f _{MX} = 8 MHz ^{Note 2} ,		Square wave input		1.1	1.7	mA		
				$V_{DD} = 2.0 \text{ V}$		Resonator connection		1.1	1.7			

- Notes 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator clock is stopped.
 - 3. When high-speed system clock is stopped
 - **4.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS(High speed main) mode: $V_{DD} = 2.7 \text{ V to } 5.5 \text{ V } @ 1 \text{ MHz to } 24 \text{ MHz}$

 $V_{DD} = 2.4 \text{ V to } 5.5 \text{ V } @ 1 \text{ MHz to } 16 \text{ MHz}$

LS(Low speed main) mode: $V_{DD} = 1.8 \text{ V to } 5.5 \text{ V } @ 1 \text{ MHz to } 8 \text{ MHz}$

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fil: high-speed on-chip oscillator clock frequency
 - **3.** Temperature condition of the TYP. value is $T_A = 25$ °C.

(2) 30-pin products

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

(1/2)

			3 0.0 V, V33 =	/						(1/2
Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply	I _{DD1}	Operating	HS (High-speed	f _{IH} = 24 MHz ^{Note 3}	Basic	V _{DD} = 5.0 V		1.5		mA
current Note 1		mode	main) mode Note 4		operation V _{DD} = 3.0 V	V _{DD} = 3.0 V		1.5		
					Normal	V _{DD} = 5.0 V		3.7	5.5	mA
					operation	V _{DD} = 3.0 V		3.7	5.5	
				f _{IH} = 16 MHz ^{Note 3}		V _{DD} = 5.0 V		2.7	4.0	mA
						V _{DD} = 3.0 V		2.7	4.0	
			LS (Low-speed	f _{IH} = 8 MHz ^{Note 3}		V _{DD} = 3.0 V		1.2	1.8	mA
		main) mode Note 4			V _{DD} = 2.0 V		1.2	1.8		
			HS (High-speed	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$		Square wave input		3.0	4.6	mA
	main) mode ^{Note 4}	main) mode Note 4	V _{DD} = 5.0 V		Resonator connection		3.2	4.8		
				$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$		Square wave input		3.0	4.6	mA
				$V_{DD} = 3.0 \text{ V}$		Resonator connection		3.2	4.8	
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$		Square wave input		1.9	2.7	mA
				$V_{DD} = 5.0 \text{ V}$		Resonator connection		1.9	2.7	
				$f_{MX} = 10 \text{ MHz}^{Note 2}$		Square wave input		1.9	2.7	mA
				V _{DD} = 3.0 V		Resonator connection		1.9	2.7	
			LS (Low-speed	$f_{MX} = 8 MHz^{Note 2}$		Square wave input		1.1	1.7	mA
	main) mode ^{Note 4} V _{DD} = 3	V _{DD} = 3.0 V		Resonator connection		1.1	1.7			
				$f_{MX} = 8 MHz^{Note 2}$		Square wave input		1.1	1.7	mA
				$V_{DD} = 2.0 \text{ V}$		Resonator connection		1.1	1.7	

- Notes 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator clock is stopped.
 - 3. When high-speed system clock is stopped
 - **4.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS(High speed main) mode: VDD = 2.7 V to 5.5 V @ 1 MHz to 24 MHz

V_{DD} = 2.4 V to 5.5 V @1 MHz to 16 MHz

LS(Low speed main) mode: $V_{DD} = 1.8 \text{ V to } 5.5 \text{ V } @ 1 \text{ MHz to } 8 \text{ MHz}$

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: high-speed on-chip oscillator clock frequency
 - **3.** Temperature condition of the TYP. value is $T_A = 25$ °C.

(2) 30-pin products

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

(2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit	
Supply	IDD2 Note 2	HALT	HS (High-speed	fin = 24 MHz ^{Note 4}	V _{DD} = 5.0 V		440	1280	μА	
current Note 1		mode	main) mode Note 6		V _{DD} = 3.0 V		440	1280		
				fin = 16 MHz ^{Note 4}	V _{DD} = 5.0 V		400	1000	μА	
					V _{DD} = 3.0 V		400	1000		
				fih = 8 MHz ^{Note 4}	V _{DD} = 3.0 V		260	530	μA	
			main) mode Note 6		V _{DD} = 2.0 V		260	530		
			main) mode Note 6	f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		280	1000	μА	
				V _{DD} = 5.0 V	Resonator connection		450	1170		
				$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		280	1000	μA	
				V _{DD} = 3.0 V	Resonator connection		450	1170		
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		190	600	μА	
				V _{DD} = 5.0 V	Resonator connection		260	670		
					$f_{MX} = 10 \text{ MHz}^{Note 3},$	Square wave input		190	600	μΑ
				V _{DD} = 3.0 V	Resonator connection		260	670		
			LS (Low-speed	fmx = 8 MHz ^{Note 3} ,	Square wave input		95	330	μΑ	
			main) mode Note 6	V _{DD} = 3.0 V	Resonator connection		145	380		
				fmx = 8 MHz ^{Note 3}	Square wave input		95	330	μΑ	
				V _{DD} = 2.0 V	Resonator connection		145	380		
	IDD3 ^{Note 5}	STOP	$T_A = -40^{\circ}C$				0.18	0.50	μА	
		mode	T _A = +25°C				0.23	0.50		
			T _A = +50°C	T _A = +50°C			0.30	1.10		
			T _A = +70°C				0.46	1.90		
			T _A = +85°C				0.75	3.30		

- Notes 1. Total current flowing into VDD, including the input leakage current flowing when the level of the input pin is fixed to VDD or Vss. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator clock is stopped.
 - 4. When high-speed system clock is stopped.
 - 5. Not including the current flowing into the 12-bit interval timer and watchdog timer.
 - **6.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as follows.

HS (High speed main) mode: VDD = 2.7 V to 5.5 V @1 MHz to 24 MHz

 $V_{DD} = 2.4 \text{ V to } 5.5 \text{ V } @ 1 \text{ MHz to } 16 \text{ MHz}$

LS (Low speed main) mode: VDD = 1.8 V to 5.5 V @1 MHz to 8 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: high-speed on-chip oscillator clock frequency
 - 3. Except STOP mode, temperature condition of the TYP. value is $T_A = 25$ °C.

(3) Peripheral functions (Common to all products)

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Low-speed onchip oscillator operating current	FIL Note 1				0.20		μΑ
12-bit interval timer operating current	ÎTMKA Notes 1, 2, 3				0.02		μΑ
Watchdog timer operating current	WDT Notes 1, 2, 4	fıL = 15 kHz			0.22		μΑ
A/D converter	IADC Notes 1, 5	When conversion at	Normal mode, AVREFP = VDD = 5.0 V		1.30	1.70	mA
operating current		maximum speed	Low voltage mode, AVREFP = VDD = 3.0 V		0.50	0.70	mA
A/D converter reference voltage operating current	ADREF Note 1				75.0		μΑ
Temperature sensor operating current	ITMPS Note 1				75.0		μА
LVD operating current	LVD Notes 1, 6				0.08		μА
Self- programming operating current	FSP Notes 1, 8				2.00	12.20	mA
BGO operating current	IBGO Notes 1, 7				2.00	12.20	mA
SNOOZE	ISNOZ Note 1	ADC operation	The mode is performed Note 9		0.50	0.60	mA
operating current			The A/D conversion operations are performed, Low voltage mode, AV _{REFP} = V _{DD} = 3.0 V		1.20	1.44	mA
		CSI/UART operation			0.70	0.84	mA

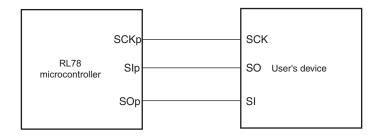
Notes 1. Current flowing to the V_{DD} .

- 2. When high speed on-chip oscillator and high-speed system clock are stopped.
- 3. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3, and IFIL and ITMKA when the 12-bit interval timer operates.
- 4. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer operates.
- **5.** Current flowing only to the A/D converter. The current value of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
- **6.** Current flowing only to the LVD circuit. The current value of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit operates.
- 7. Current flowing only during data flash rewrite.
- 8. Current flowing only during self programming.
- 9. For shift time to the SNOOZE mode, see 17.3.3 SNOOZE mode.

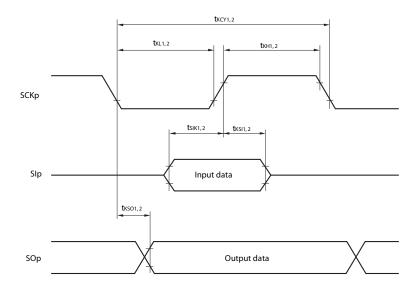
Remarks 1. fil: Low-speed on-chip oscillator clock frequency

2. Temperature condition of the TYP. value is $T_A = 25$ °C

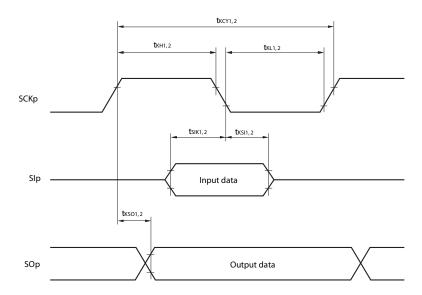
CSI mode connection diagram (during communication at same potential)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



(Remarks are listed on the next page.)

(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCK00... internal clock output, corresponding CSI00 only)

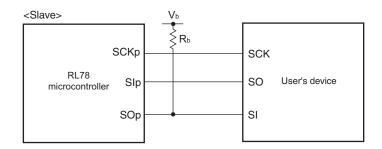
(Ta = -40 to +85°C, 2.7 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Symbol Conditions		` `	HS (high-speed main) Mode		LS (low-speed main) Mode	
				MIN.	MAX.	MIN.	MAX.	
SCK00 cycle time	tkcy1	tkcy1 ≥ 2/fCLK	$\begin{aligned} &4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \\ &2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ &C_{\text{b}} = 20 \text{ pF}, \text{ R}_{\text{b}} = 1.4 \text{ k}\Omega \end{aligned}$	200		1150		ns
			$\begin{split} 2.7 & \ V \le V_{DD} < 4.0 \ V, \\ 2.3 & \ V \le V_b \le 2.7 \ V, \\ C_b = 20 & \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	300		1150		ns
SCK00 high-level width	tкн1	$4.0 \text{ V} \le \text{V}_{DD} \le 5.$ $C_b = 20 \text{ pF}, R_b =$	5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 k Ω	tксу1/2 — 50		tксу1/2- 50		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b =$	$0 \text{ V}, 2.3 \text{ V} \le V_b \le 2.7 \text{ V},$ = $2.7 \text{ k}\Omega$	tксу1/2 — 120		tксу1/2 – 120		ns
SCK00 low-level width	t _{KL1}	$4.0~V \leq V_{DD} \leq 5.$ $C_b = 20~pF,~R_b =$	5 V, 2.7 V \leq Vb \leq 4.0 V, = 1.4 k Ω	tксу1/2 — 7		tксү1/2 – 50		ns
		$\label{eq:2.7} \begin{array}{l} 2.7 \ V \leq V_{DD} < 4.0 \ V, \ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ \\ C_b = 20 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		tксу1/2 — 10		tксү1/2 – 50		ns
SI00 setup time tsik1		$\label{eq:continuous} 4.0~V \leq V_{DD} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ $C_b = 20~pF,~R_b = 1.4~k\Omega$		58		479		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b =$	0 V, 2.3 V \leq Vb \leq 2.7 V, = 2.7 k Ω	121		479		ns
SI00 hold time (from SCK00↑) Note 1	tksi1	$4.0 \text{ V} \leq \text{V}_{DD} \leq 5.$ $C_b = 20 \text{ pF}, \text{ R}_b =$	5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 kΩ	10		10		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b =$	0 V, 2.3 V \leq V _b \leq 2.7 V, = 2.7 kΩ	10		10		ns
Delay time from SCK00↓ to SO00 output Note 1	tkso1	$4.0 \text{ V} \le V_{DD} \le 5.$ $C_b = 20 \text{ pF}, R_b =$	5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 kΩ		60		60	ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b =$	0 V, 2.3 V \leq V _b \leq 2.7 V, = 2.7 kΩ		130		130	ns
SI00 setup time (to SCK00↓) Note 2	tsıĸı	$4.0 \text{ V} \leq \text{V}_{DD} \leq 5.$ $C_b = 20 \text{ pF, R}_b =$	5 V, 2.7 V \leq Vb \leq 4.0 V, $= 1.4 \ k\Omega$	23		110		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b =$	0 V, 2.3 V \leq Vb \leq 2.7 V, = 2.7 k Ω	33		110		ns
SI00 hold time (from SCK00↓) Note 2	tksıı	$4.0 \text{ V} \leq \text{V}_{DD} \leq 5.$ $C_b = 20 \text{ pF}, \text{ R}_b =$	5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 k Ω	10		10		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b =$	0 V, 2.3 V \leq Vb \leq 2.7 V, = 2.7 k Ω	10		10		ns
Delay time from SCK00↑ to SO00 output Note 2	t _{KSO1}	$4.0~V \leq V_{DD} \leq 5.$ $C_b = 20~pF,~R_b =$	5 V, 2.7 V \leq Vb \leq 4.0 V, $=$ 1.4 k Ω		10		10	ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b =$	0 V, 2.3 V \leq Vb \leq 2.7 V, = 2.7 k Ω		10		10	ns

(Notes, Caution, and Remarks are listed on the next page.)

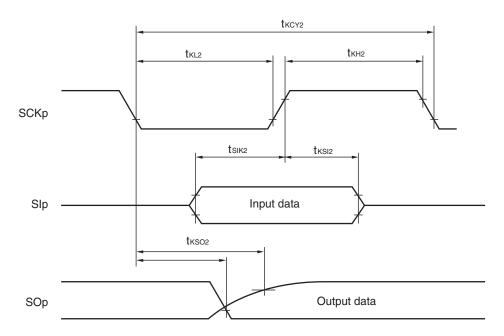


CSI mode connection diagram (during communication at different potential)



- **Remarks 1.** Rb $[\Omega]$: Communication line (SOp) pull-up resistance, Cb [F]: Communication line (SOp) load capacitance, Vb [V]: Communication line voltage
 - 2. p: CSI number (p = 00, 20), m: Unit number (m = 0, 1), n: Channel number (n = 0)
 - 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the serial clock select register m (SPSm) and the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 10))

CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



- **Notes 1.** Excludes quantization error ($\pm 1/2$ LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - **3.** When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AVREFP = VDD.

- **4.** Values when the conversion time is set to 57 μ s (min.) and 95 μ s (max.).
- 5. Refer to 28.6.2 Temperature sensor/internal reference voltage characteristics.

(2) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI16 to ANI22

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{AV}_{REFP} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V}, \text{Reference voltage (+)} = \text{AV}_{REFP}, \text{Reference voltage (-)} = \text{AV}_{REFM} = 0 \text{ V})$

Parameter	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit
Resolution	Res			8		10	bit
Overall error Note 1	AINL	10-bit resolution	10-bit resolution		1.2	±5.0	LSB
		AVREFP = VDD Note 3			1.2	±8.5 Note 4	LSB
Conversion time	tconv	Target ANI pin: ANI16 to ANI22	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
			$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μS
		$1.8~V \leq V_{DD} \leq 5.5~V$	17		39	μS	
				57		95	μS
Zero-scale error Notes 1, 2	EZS	10-bit resolution				±0.35	%FSR
		$AV_{REFP} = V_{DD}^{Note 3}$				±0.60 Note 4	%FSR
Full-scale error Notes 1, 2	EFS	10-bit resolution				±0.35	%FSR
		$AV_{REFP} = V_{DD}^{Note 3}$				±0.60 Note 4	%FSR
Integral linearity error Note 1	ILE	10-bit resolution				±3.5	LSB
		AVREFP = V _{DD} Note 3				±6.0 Note 4	LSB
Differential linearity	DLE	10-bit resolution				±2.0	LSB
error $^{Note 1}$ $AV_{REFP} = V_{DD}^{Note 3}$		AVREFP = VDD Note 3				±2.5 Note 4	LSB
Analog input voltage	VAIN	ANI16 to ANI22		0		AVREFP and VDD	V

- **Notes 1.** Excludes quantization error ($\pm 1/2$ LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - **3.** When $AV_{REFP} \leq V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 4.0 LSB to the MAX, value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.20\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ±2.0 LSB to the MAX. value when AVREFP = VDD.

4. When the conversion time is set to 57 μ s (min.) and 95 μ s (max.).



(2/4)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low ^{Note 1}	lo _{L1}	20-, 24-pin products: Per pin for P00 to P03 ^{Note 4} , P10 to P14, P40 to P42 30-pin products:				8.5 Note 2	mA
		Per pin for P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147					
		Per pin for P60, P61				15.0 Note 2	mA
		20-, 24-pin products:	$4.0~V \leq V_{DD} \leq 5.5~V$			25.5	mA
		Total of P40 to P42 30-pin products: Total of P00, P01, P40, P120 (When duty ≤ 70% Note 3)	$2.7~V \leq V_{DD} < 4.0~V$			9.0	mA
			2.4 V ≤ V _{DD} < 2.7 V			1.8	mA
		20-, 24-pin products:	$4.0~V \leq V_{DD} \leq 5.5~V$			40.0	mA
			$2.7~V \leq V_{DD} < 4.0~V$			27.0	mA
lou		P10 to P14, P60, P61 30-pin products: Total of P10 to P17, P30, P31, P50, P51, P60, P61, P147 (When duty ≤ 70% Note 3)	2.4 V ≤ V _{DD} < 2.7 V			5.4	mA
		Total of all pins (When duty ≤ 70% Note 3)				65.5	mA
	lol2	Per pin for P20 to P23				0.4	mA
		Total of all pins				1.6	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the Vss pin.
 - 2. However, do not exceed the total current value.
 - 3. The output current value under conditions where the duty factor \leq 70%.

If duty factor > 70%: The output current value can be calculated with the following expression (where n represents the duty factor as a percentage).

- Total output current of pins = $(IoL \times 0.7)/(n \times 0.01)$
- <Example> Where n = 80% and IoL = 10.0 mA

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7 \text{ mA}$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

4. 24-pin products only.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

(3/4)

Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit	
Input voltage, high	V _{IH1}	Normal input buffer 20-, 24-pin products: P00 to P03 ^{Note 2} , P10 to P14, P40 to P42		0.8V _{DD}		V_{DD}	V
		30-pin products: P00, P01, P1 P40, P50, P51, P120, P147	0 to P17, P30, P31,				
	V _{IH2}	TTL input buffer	$4.0~V \leq V_{\text{DD}} \leq 5.5~V$	2.2		V _{DD}	V
		20-, 24-pin products: P10, P11	$3.3 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$	2.0		V _{DD}	٧
		30-pin products: P01, P10, P11, P13 to P17	2.4 V ≤ V _{DD} < 3.3 V	1.5		V _{DD}	V
	VIH3	Normal input buffer P20 to P23		0.7V _{DD}		V _{DD}	V
	V _{IH4}	P60, P61		0.7V _{DD}		6.0	V
	V _{IH5}	P121, P122, P125 ^{Note 1} , P137, EXCLK, RESET		0.8V _{DD}		V_{DD}	٧
Input voltage, low	V _{IL1}	Normal input buffer 20-, 24-pin products: P00 to P03 ^{Note 2} , P10 to P14, P40 to P42 30-pin products: P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147		0		0.2V _{DD}	V
	V _{IL2}	TTL input buffer	$4.0~V \leq V_{DD} \leq 5.5~V$	0		0.8	V
		20-, 24-pin products: P10, P11	$3.3 \text{ V} \leq \text{V}_{\text{DD}} < 4.0 \text{ V}$	0		0.5	٧
		30-pin products: P01, P10, P11, P13 to P17	2.4 V ≤ V _{DD} < 3.3 V	0		0.32	V
	V _{IL3}	P20 to P23		0		0.3V _{DD}	٧
	V _{IL4}	P60, P61		0		0.3V _{DD}	٧
	V _{IL5}	P121, P122, P125 ^{Note 1} , P137, I	EXCLK, RESET	0		0.2V _{DD}	V
Output voltage, high	V _{OH1}	20-, 24-pin products: P00 to P03 ^{Note 2} , P10 to P14,	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ Iон1 = -3.0 mA	V _{DD} -0.7			V
		P40 to P42 30-pin products:	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH1} = -2.0 \text{ mA}$	V _{DD} -0.6			V
		P00, P01, P10 to P17, P30, P31, P40, P50, P51, P120, P147	$2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH1} = -1.5 \text{ mA}$	V _{DD} -0.5			V
	V _{OH2}	P20 to P23	Іон2 = -100 μΑ	V _{DD} -0.5			V

Notes 1. 20, 24-pin products only.

2. 24-pin products only.

Caution The maximum value of V_{IH} of pins P10 to P12 and P41 for 20-pin products, P01, P10 to P12, and P41 for 24-pin products, and P00, P10 to P15, P17, and P50 for 30-pin products is V_{DD} even in N-ch open-drain mode. High level is not output in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter Symbol		Conditions		HS (high-speed main) Mode		Unit
			MIN.	MAX.		
Transfer rate Note4	Reception	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V}$		fMCK/12 Note 1	bps	
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 2}$		2.0	Mbps
			$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V}$		fMCK/12 Note 1	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note \ 2}$		2.0	Mbps
	$2.4 \text{ V} \le \text{V}_{DD} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V}$		fMCK/12 Note 1	bps		
		Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note \ 2}$		2.0	Mbps	
	Transmission	$4.0 \text{ V} \le V_{DD} \le 5.5 \text{ V},$ $2.7 \text{ V} \le V_b \le 4.0 \text{ V}$		Note 3	bps	
		Theoretical value of the maximum transfer rate $C_b = 50$ pF, $R_b = 1.4$ k Ω , $V_b = 2.7$ V		2.0 Note 4	Mbps	
			$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V},$		Note 5	bps
	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega, V_b = 2.3 \text{ V}$		1.2 Note 6	Mbps		
		$2.4 \text{ V} \le \text{V}_{DD} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V}$		Notes 2, 7	bps	
			Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6 \text{ V}$		0.43 Note 8	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 24 MHz (2.7 V \leq VDD \leq 5.5 V)

16 MHz (2.4 V
$$\leq$$
 V_{DD} \leq 5.5 V)

3. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq VDD \leq 5.5 V and 2.7 V \leq Vb \leq 4.0 V

$$\label{eq:maximum transfer rate} \text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \text{ln } (1-\frac{2.2}{V_b})\} \times 3} \text{ [bps]}$$

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)

(Ta = -40 to +105°C, 2.4 V \leq VDD \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Conditions		HS (high-speed	d main) Mode	Unit
				MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$4.0~V \leq V_{DD} \leq 5.5~V,$	600		ns
			$2.7~V \leq V_b \leq 4.0~V,$			
			$C_b=30~pF,~R_b=1.4~k\Omega$			
			$2.7 \text{ V} \le \text{V}_{DD} < 4.0 \text{ V},$	1000		ns
			$2.3~V \leq V_b \leq 2.7~V,$			
			$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
			$2.4 \text{ V} \le \text{V}_{DD} < 3.3 \text{ V},$	2300		ns
			$1.6 \text{ V} \le V_b \le 2.0 \text{ V},$			
			$C_b = 30$ pF, $R_b = 5.5$ k Ω			
SCKp high-level width	t _{KH1}	$4.0 \; V \leq V_{DD} \leq 5.5 \; V, 2.7 \; V \leq V_b \leq 4.0 \; V,$		tксу1/2 -150		ns
		C _b = 30 pF, R _b	$_{0}$ = 1.4 k Ω			
		2.7 V ≤ V _{DD} < 4	$4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$	tkcy1/2 -340		ns
		C _b = 30 pF, R _b	$_{0}$ = 2.7 k Ω			
		2.4 V ≤ V _{DD} < 3	$3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_b \le 2.0 \text{ V},$	tkcy1/2 -916		ns
		C _b = 30 pF, R _b	$_{0}$ = 5.5 k Ω			
SCKp low-level width	t _{KL1}	-	$5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$	tkcy1/2 -24		ns
		Сь = 30 pF, R				
			$4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$	tkcy1/2 -36		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$		1.0.1/2 00		0
		$2.4 \text{ V} \le \text{V}_{DD} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V},$		tксү1/2 –100		ns
	$2.4 \text{ V} \le \text{VDD} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{Vb} \le 2.0$ $C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$		•	IKCY1/2 - 100		115
		$C_0 = 30 \text{ pr}, \text{ Re}$	0.0 K22			

- Cautions 1. Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register 1 (PIM1) and port output mode register 1 (POM1). For VIH and VIL, see the DC characteristics with TTL input buffer selected.
 - 2. CSI01 and CSI11 cannot communicate at different potential.
- **Remarks 1.** R_b [Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b [F]: Communication line (SCKp, SOp) load capacitance, V_b [V]: Communication line voltage
 - **2.** p: CSI number (p = 00, 20)

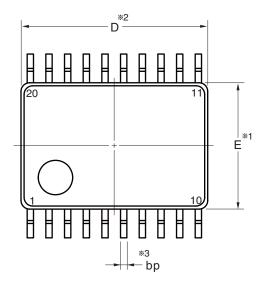
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4. PACKAGE DRAWINGS

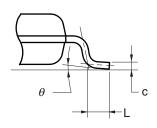
4.1 20-pin products

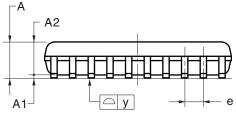
R5F1026AASP, R5F10269ASP, R5F10268ASP, R5F10267ASP, R5F10266ASP R5F1036AASP, R5F10369ASP, R5F10368ASP, R5F10367ASP, R5F10366ASP R5F1026ADSP, R5F10269DSP, R5F10268DSP, R5F10267DSP, R5F10266DSP R5F1036ADSP, R5F10369DSP, R5F10368DSP, R5F10367DSP, R5F10366DSP R5F1026AGSP, R5F10269GSP, R5F10268GSP, R5F10267GSP, R5F10266GSP

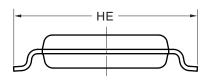
JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP20-4.4x6.5-0.65	PLSP0020JB-A	P20MA-65-NAA-1	0.1



detail of lead end







NOTE

- 1.Dimensions "X1" and "X2" do not include mold flash.
- 2.Dimension "X3" does not include trim offset.

	(UNIT:mm)
ITEM	DIMENSIONS
D	6.50±0.10
E	4.40±0.10
HE	6.40±0.20
Α	1.45 MAX.
A1	0.10±0.10
A2	1.15
е	0.65±0.12
bp	$0.22 + 0.10 \\ -0.05$
С	$0.15 + 0.05 \\ -0.02$
L	0.50±0.20
У	0.10
θ	0° to 10°

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